ABSTRACT

A semiconductor device including a drift layer of a first conductivity type formed on a surface of a semiconductor substrate. A surface of the drift layer has a second area positioned on an outer periphery of a first area. A cell portion formed in the first area includes a first base layer of a second conductivity type, a source layer and a control electrode formed in the first base layer and the source layer. The device also includes a terminating portion formed in the drift layer including a second base layer of a second conductivity type, an impurity diffused layer of a second conductivity type, and a metallic compound whose end surface on the terminating portion side is positioned on the cell portion side away from the end surface of the impurity diffused layer on the terminal portion side.